



Mechanical Data		Notes		
Dice size		Ax:380um,Ay:430um,Bx:180um,By:230um		
Wafer size		4"		
Chip Thickness		138um±12um		
Scribe line width		60um		
Top metal		Al for wire bonding,d=2.2um±0.2um		
Back side metal		Ti-Ni-Ag for soldering		
Parameter	Symbol	Conditions	Value	Unit
Reverse stand-off voltage	VRWM		5.0	V
Peak pulse power	PPP	Tp=8/20us	130	W
Peak pulse current	IPP	Tp=8/20us	12.0	A
Electrostatic discharge	VESD	IEC61000-4-2 Level 4	± 15(AIR)	KV
Max.junction temp.	Tj		+150	°C

Characteristics TA=25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Breakdown Voltage	VBR	IT=1mA	5.6		9.4	V
Reverse leakage current	IR	VR=5V			0.09	uA
Clamping voltage	VC	IPP=1.0A IPP=12A			10.0 14.0	V
Diode capacitand pin1 to 2	Cj	VR=0V f=1MHZ		24.0	30.0	pf

Notes:

- (1)sampling testing:no bad dice inking/guaranteed good die >93%
- (2)Testing follow customer
- (3) $T_j = T_a + R_{th(j-a)} * (P_f + P_r)$, where $R_{th(j-a)}$ -thermal resistance, P_f -forward power dissipation,
 P_r -revers power dissipation
- (4)**For device testing